

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of Chang Gyu KIM et al.) METHOD FOR FORMING ISOLATION
Korean Application No. 2001-15415) LAYER OF SEMICONDUCTOR DEVICE
Korean Filing Date: March 24, 2001)
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)

PRELIMINARY AMENDMENT

CLEAN VERSION OF ABSTRACT

Assistant Commissioner for Patents
Washington, D.C. 20231

Dear Sir:

Please amend the subject application as follows:

In the Specification

--CROSS REFERENCE TO RELATED APPLICATION

This application claims the priority of Korean patent application Serial No. 2001-15415
filed on March 24, 2001.-

In the Abstract

Please replace the abstract presently on file with the new abstract presented herewith.

ABSTRACT OF THE DISCLOSURE

A method in which, a silicon substrate in which an active region and a field region are defined is provided, and a trench is formed in the silicon substrate within the field region. An insulating layer to be used as the isolation layer is then formed on the silicon substrate including the trench. Thus the trench is filled with the insulating layer. Next, a capping layer is formed on

a resultant entire structure including the insulating layer, and selectively removed to expose an upper portion of the insulating layer in the active region. The exposed insulating layer in the active region is then removed by a first wet etching, and the residual capping layer is removed by a second wet etching. Accordingly, the isolation layer is obtained from the insulating layer remaining in the trench.

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